

QST-3062

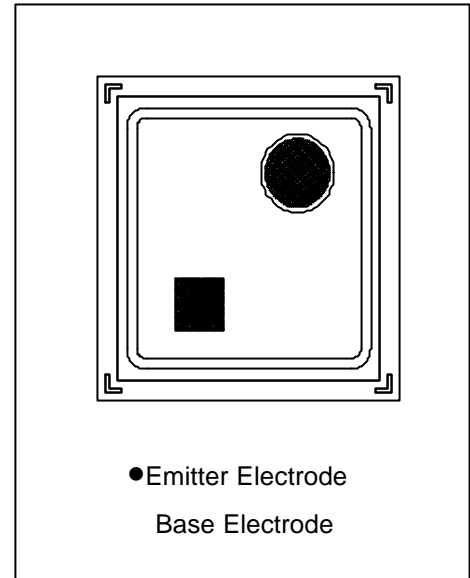
SILICON PHOTOTRANSISTOR

LOW SATURATION NPN PHOTOTRANSISTOR

HIGH STABLE LINEALITY

HIGH SPEED SWITCHING

- **DIE SIZE** 0.62mm × 0.62mm
- **DIE THICKNESS** 280 ± 20μm
- **METALLIZATION**
 - TOP Al
 - BOTTOM Au
- **PASSIVATION** Silicon Nitride
- **BONDING PAD SIZE**
 - BASE □100μm × 100μm
 - EMITTER φ130μm



ABSOLUTE MAXIMUM RATINGS (Ta= 25° C)

Parameter	Symbol	Maximum rating	Unit
Reverse Breakdown Voltage	B _{VR}	30	V
Junction Temperature	T _J	5	°C

ELECTRICAL / OPTICAL CHARACTERISTICS (Ta= 25° C)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
C-E Leake Current	I _{CEO}	V _{CE} =10V			100	nA
Spectrum Sensitivity	λ		450	~ 1,100		nm
Peak Sensing Wavelength	λ _P			880		nm
C-E Saturation Voltage	V _{CES}	I _C =5mA, I _B =1mA			250	mV
C-E Voltage	BV _{CEO}	I _{CE} =500μA	40			V
C-B Voltage	BV _{CBO}	I _{CB} =50μA	50			V
E-B Voltage	BV _{EBO}	I _{EB} =50μA	6	1.4	1.5	V
E-C Voltage	BV _{ECO}	I _{EC} =50μA	5	10	50	V
DC Current Gain 1	H _{FE1}	V _{CE} =10V, I _C =1mA	200		1500	-
DC Current Gain 2	h _{FE2}	V _{CE} =10V, I _C =0.1mA	200			-
Lineality	h _{FE}	h _{FE1} / h _{FE2}			1.15	-

Note(1): h FE Rank : A (200~500), B (500~900), C(900~1500).



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